



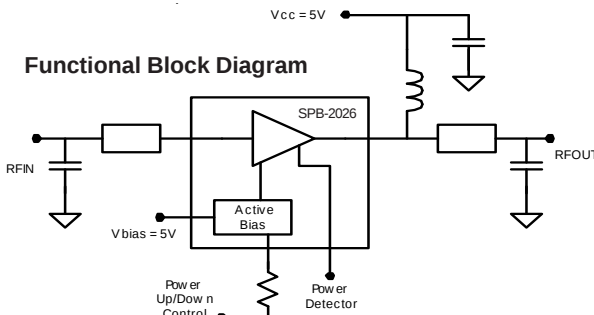
## Product Description

RFMD's SPB2026Z is a high linearity single-stage class AB Heterojunction Bipolar Transistor (HBT) amplifier housed in a surface-mountable plastic encapsulated package. This HBT amplifier is made with InGaP on GaAs device technology and fabricated with MOCVD for an ideal combination of low cost and high reliability. This product is well suited for use as a driver stage in macro/micro-cell infrastructure equipment or as the final output stage in pico-cell infrastructure equipment. It can run from a 3V to 6V supply. It is prematched to  $\sim 5\Omega$  on the input for broadband performance and ease of matching at the board level. It features an input power detector, on/off power control, ESD protection, excellent overall robustness and a hand reworkable and thermally enhanced S0F-26 package. This product is RoHS and WEEE compliant.

### Optimum Technology Matching® Applied

- ☐ GaAs HBT
- ☐ GaAs MESFET
- ☒ InGaP HBT
- ☐ SiGe BiCMOS
- ☐ Si BiCMOS
- ☐ SiGe HBT
- ☐ GaAs pHEMT
- ☐ Si CMOS
- ☐ Si BJT
- ☐ GaN HEMT
- ☐ RF MEMS

Functional Block Diagram



## Features

- $P_{1dB} = 33.8\text{dBm}$  at 5V, 1960MHz
- $ACP = -45\text{dBc}$  with 25 dBm Channel Power at 1960MHz
- On-Chip Input Power Detector
- Low Thermal Resistance Package
- Power Up/Down Control  $< 1\mu\text{s}$
- Robust Class 1C ESD

## Applications

- Macro/Micro-Cell Driver Stage
- Pico-Cell Output Stage
- GSM, CDMA, TDSCDMA, WCDMA
- Single and Multi-Carrier Applications

| Parameter                       | Specification |             |       | Unit                 | Condition                                                           |
|---------------------------------|---------------|-------------|-------|----------------------|---------------------------------------------------------------------|
|                                 | Min.          | Typ.        | Max.  |                      |                                                                     |
| Small Signal Gain               |               | 13.6        |       | dB                   | 1842MHz                                                             |
|                                 | 12.2          | 13.7        | 15.2  | dB                   | 1960MHz                                                             |
|                                 | 12.1          | 13.6        | 15.1  | dB                   | 2140MHz                                                             |
| Output Power at 1dB Compression |               | 33.9        |       | dBm                  | 1842MHz                                                             |
|                                 |               | 33.8        |       | dBm                  | 1960MHz                                                             |
|                                 | 31.3          | 32.8        |       | dBm                  | 2140MHz                                                             |
| Third Order Supression          |               | -49.0       |       | dBc                  | 1842MHz, 22dBm per tone, 1MHz spacing                               |
|                                 | -42.0         | -45.0       |       | dBc                  | 1960MHz, 22dBm per tone, 1MHz spacing                               |
|                                 |               | -48.0       |       | dBc                  | 2140MHz, 22dBm per tone, 1MHz spacing                               |
| WCDMA Channel Power             |               | -55.0       |       | dBc ACP              | 1842MHz, tested with 64 Channels, FWD, 23dBm                        |
|                                 |               | -55.0       |       | dBc ACP              | 1960MHz, tested with 64 Channels, FWD, 23dBm                        |
|                                 |               | -55.0       | -48.0 | dBc ACP              | 2140MHz, tested with 64 Channels, FWD, 23dBm                        |
| WCDMA Channel Power             |               | -45.0       |       | dBc ACP              | 1842MHz, 1960MHz, and 2140MHz. Tested with 64 Channels, FWD, 25dBm. |
| Input Return Loss               | 11.0          | 14.0        |       | dB                   | 1930MHz to 1990MHz                                                  |
| Output Return Loss              | 9.0           | 12.0        |       | dB                   | 1930MHz to 1990MHz                                                  |
| Noise Figure                    |               | 5.2         | 6.2   | dB                   | 1960MHz                                                             |
| Voltage Range                   |               | 0.85 to 1.4 |       | V                    | CW $P_{OUT} = 13\text{dBm}$ to $33\text{dBm}$                       |
| Thermal Resistance              |               | 12.0        |       | $^{\circ}\text{C/W}$ | junction - lead                                                     |
| Quiescent Current               | 380           | 445         | 500   | mA                   | $V_{CC} = 5\text{V}$                                                |
| Power up Control Current        |               | 2.1         |       | mA                   | $V_{PC} = 5\text{V}$                                                |
| $V_{CC}$ Leakage Current        |               |             | 100   | uA                   | $V_{CC} = 5\text{V}$ , $V_{PC} = 0\text{V}$                         |

Test Conditions:  $V_{CC} = 5\text{V}$ ,  $I_{CQ} = 445\text{mA}$  Typ.,  $T_L = 25^{\circ}\text{C}$ ,  $Z_S = Z_L = 50\Omega$

Absolute Maximum Ratings

| Parameter                                                             | Rating     | Unit |
|-----------------------------------------------------------------------|------------|------|
| Device Current (I <sub>CE</sub> )                                     | 1500       | mA   |
| *Device Voltage (V <sub>CC</sub> )                                    | 7          | V    |
| RF Input Power with 50Ω output load                                   | 28         | dBm  |
| RF Input Power with 10:1 VSWR output load                             | 23         | dBm  |
| RF Output Power with 50Ω output load (Continuous long term operation) | 30         | dBm  |
| Junction Temp (T <sub>J</sub> )                                       | +150       | °C   |
| Operating Temp Range (T <sub>L</sub> )                                | -40 to +85 | °C   |
| Storage Temp                                                          | +150       | °C   |
| Power Dissipation (P <sub>DISS</sub> )                                | 6          | W    |
| ESD Rating - Human Body Model (HBM)                                   | Class 1C   |      |
| Moisture Sensitivity Level                                            | MSL 1      |      |

\*Note: No RF Drive  
Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.  
Bias Conditions should also satisfy the following expression:  
 $I_D V_D < (T_J - T_L) / R_{TH}$ ,  $J-I$  and  $T_L = T_{LEAD}$

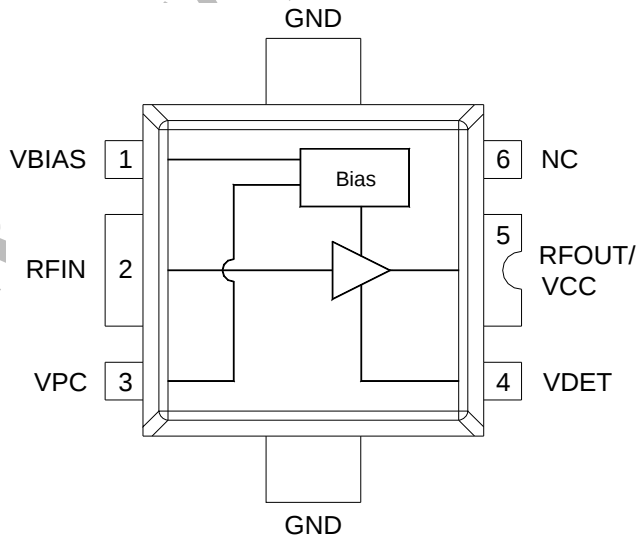
 **Caution!** ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

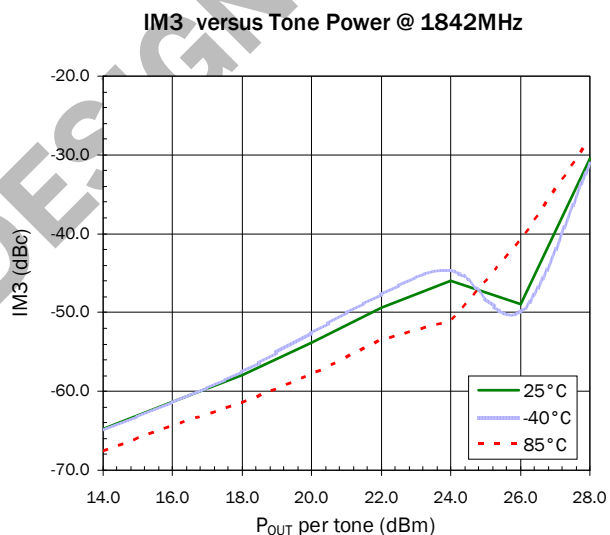
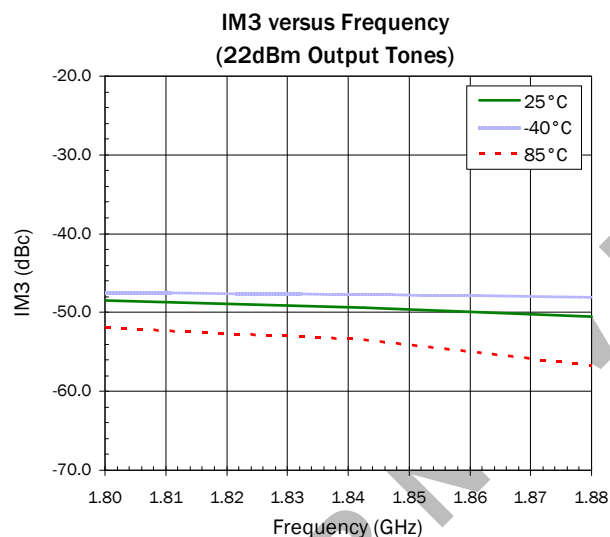
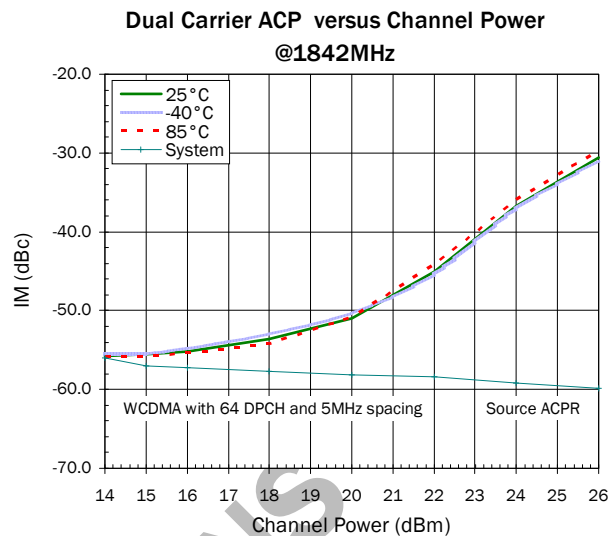
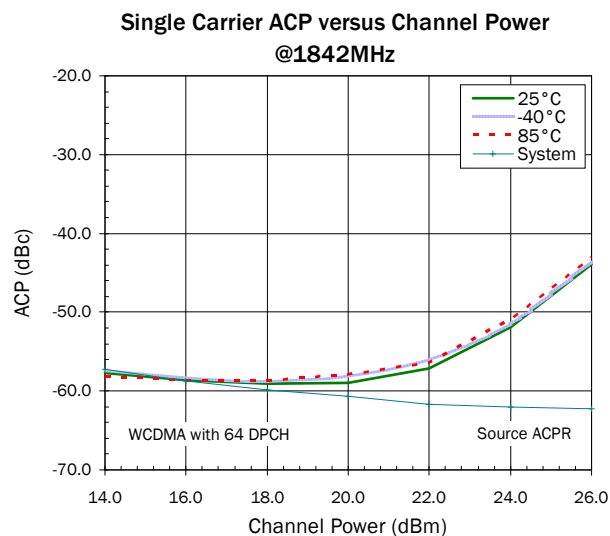
RoHS status based on EU Directive 2002/95/EC (at time of this document revision).

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Simplified Device Schematic

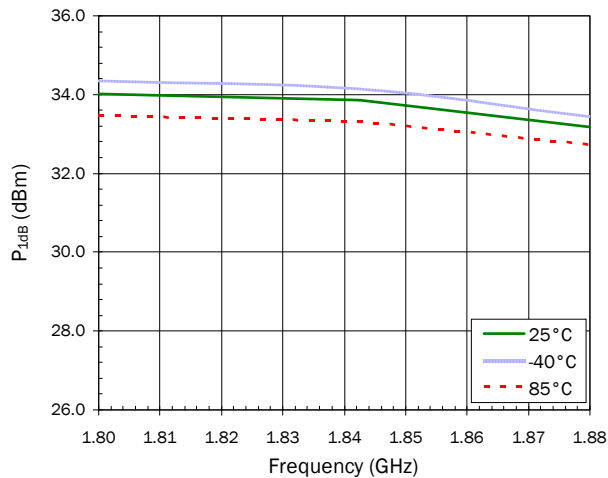


## Typical RF Performance (1805MHz to 1880MHz Application Circuit)

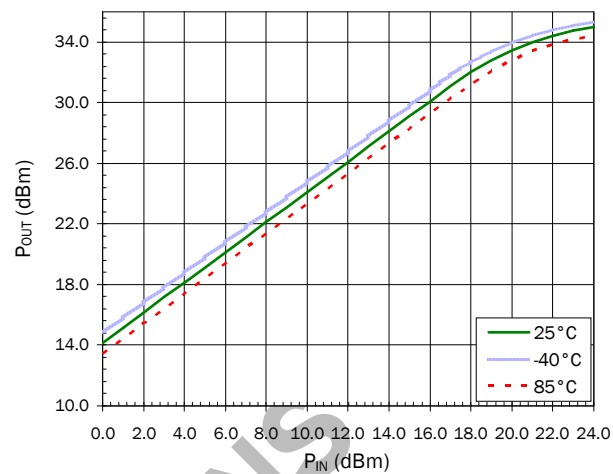


## Typical RF Performance (1805MHz to 1880MHz Application Circuit)

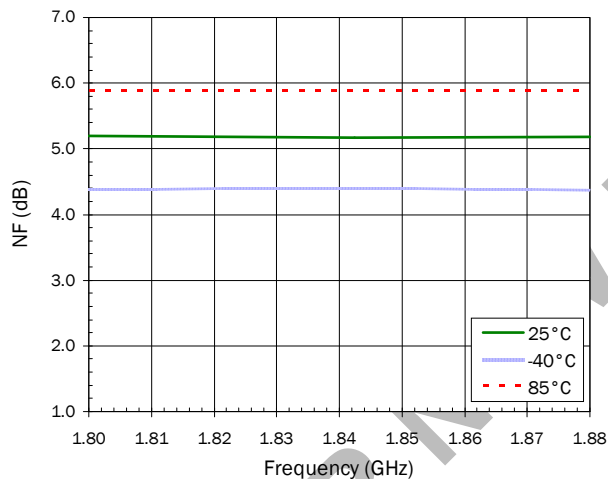
$P_{1dB}$  versus Frequency



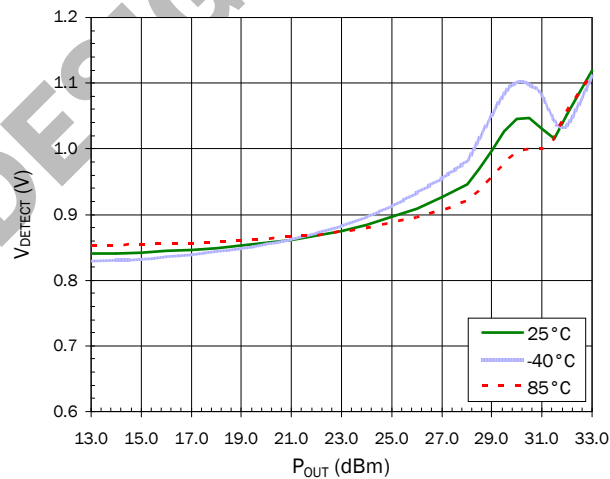
$P_{IN}$  versus  $P_{OUT}$  @ 1842MHz



Noise Figure vs. Frequency

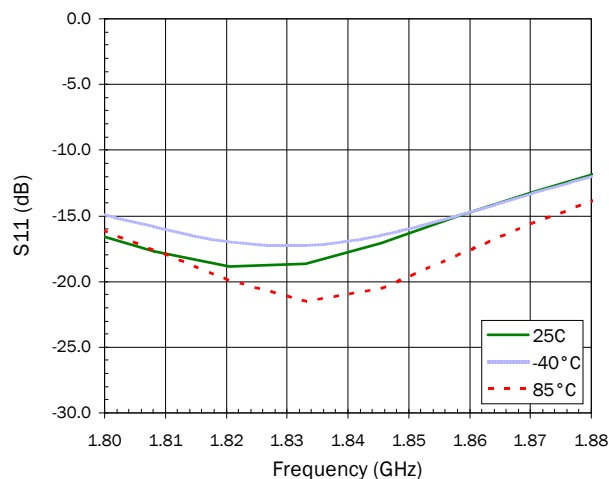


$V_{DETECT}$  versus  $P_{OUT}$  @ 1842MHz

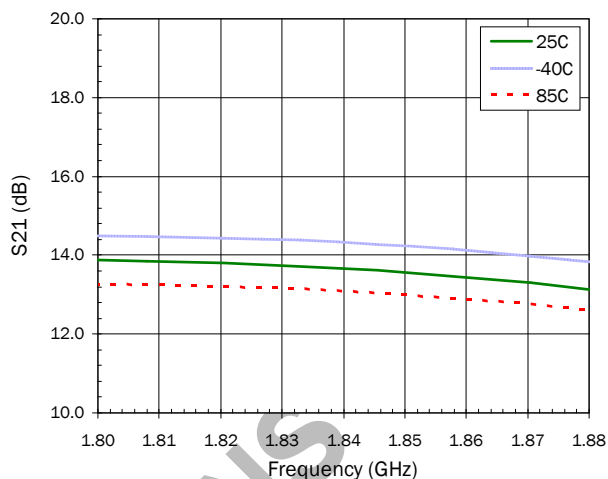


## S-Parameters Over Temperature (1805MHz to 1880MHz Application Circuit)

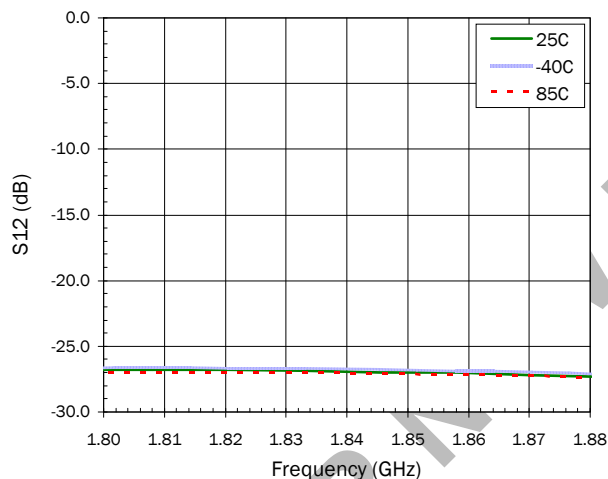
**S11 over Temperature**



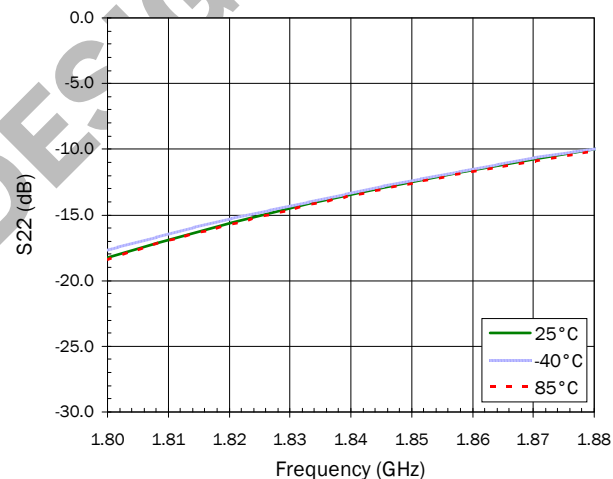
**S21 over Temperature**



**S12 over Temperature**

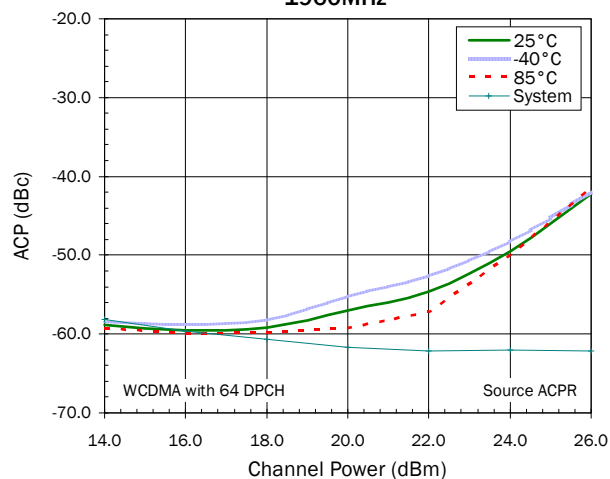


**S22 over Temperature**

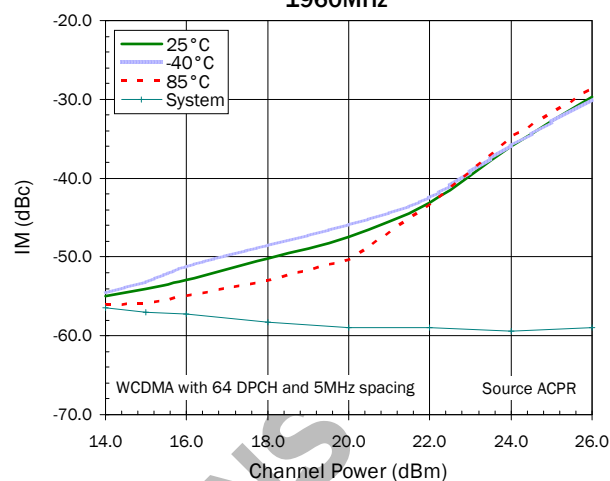


## Typical RF Performance (1930MHz to 1990MHz Application Circuit)

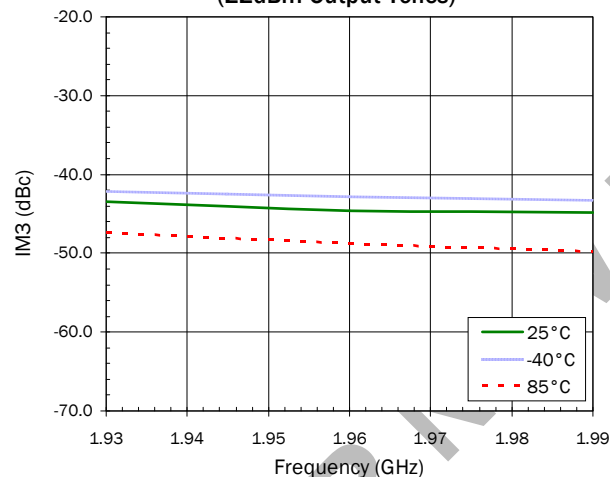
Single Carrier ACP versus Channel Power @  
1960MHz



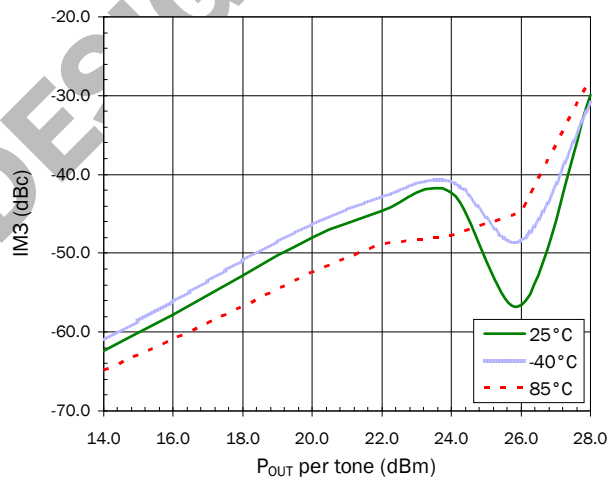
Dual Carrier ACP versus Channel Power @  
1960MHz



IM3 versus Frequency  
(22dBm Output Tones)

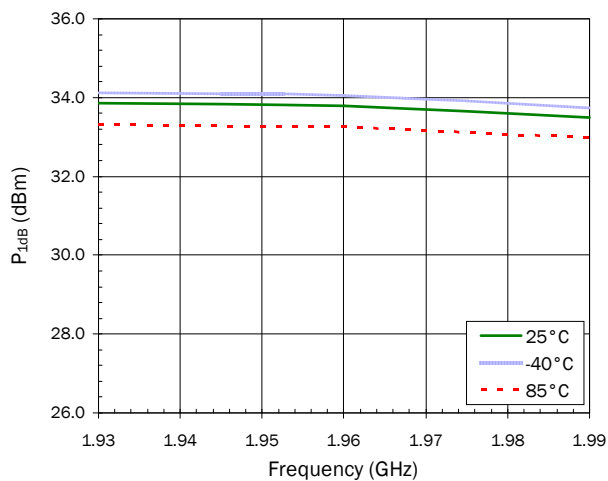


IM3 versus Tone Power @ 1960MHz

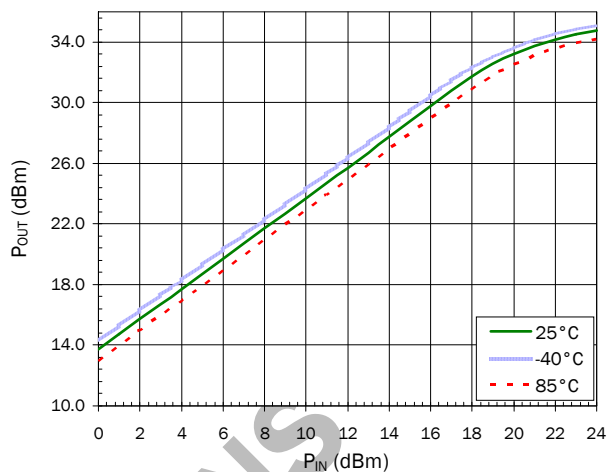


## Typical RF Performance (1930MHz to 1990MHz Application Circuit)

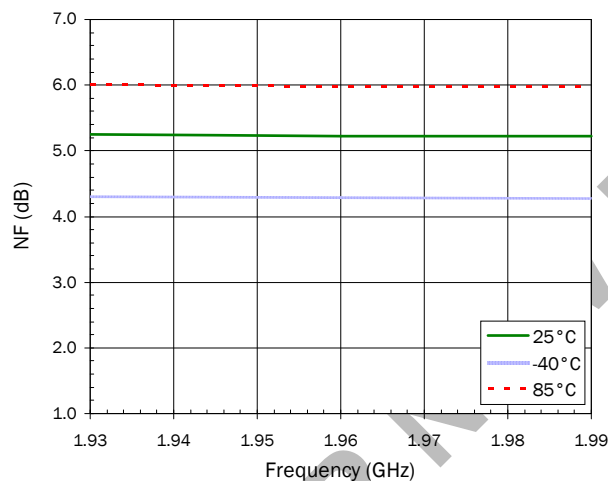
**$P_{1dB}$  versus Frequency**



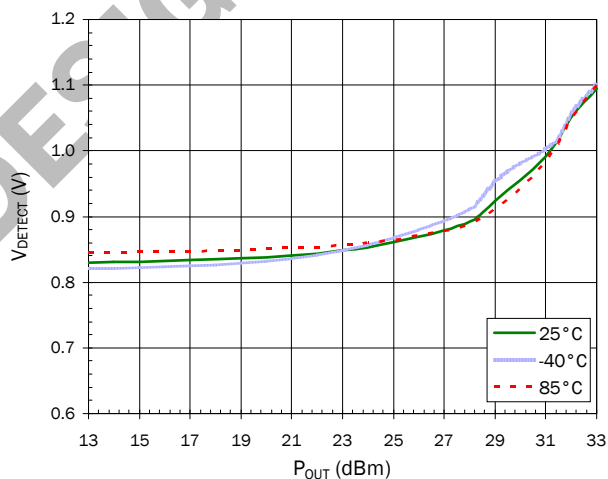
**$P_{IN}$  versus  $P_{OUT}$  @ 1960MHz**



**Noise Figure versus Frequency**

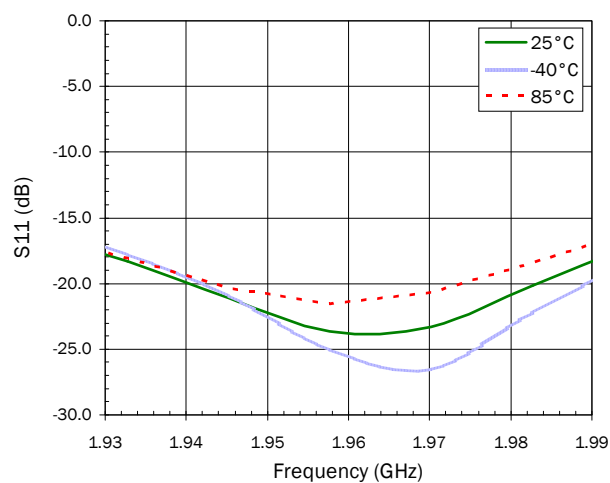


**$V_{DETECT}$  versus  $P_{OUT}$  @ 1960MHz**

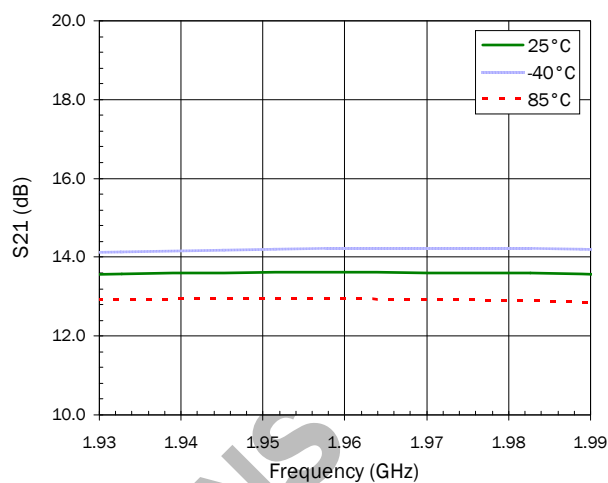


## S-Parameters over Temperature (1930MHz to 1990MHz Application Circuit)

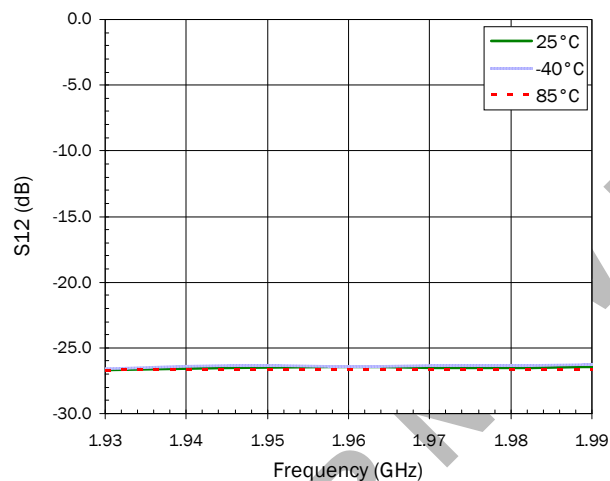
**S11 over Temperature**



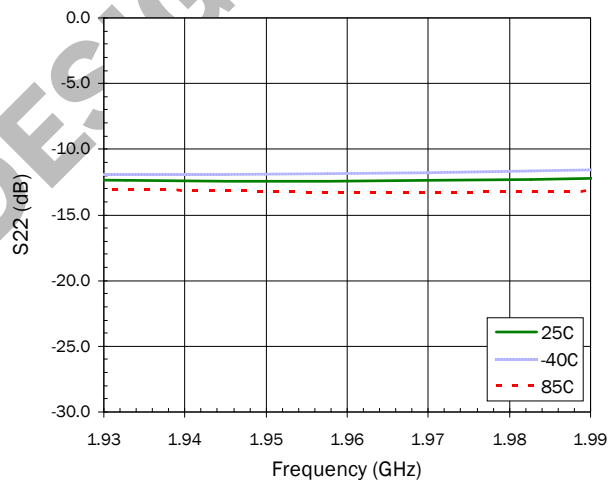
**S21 over Temperature**



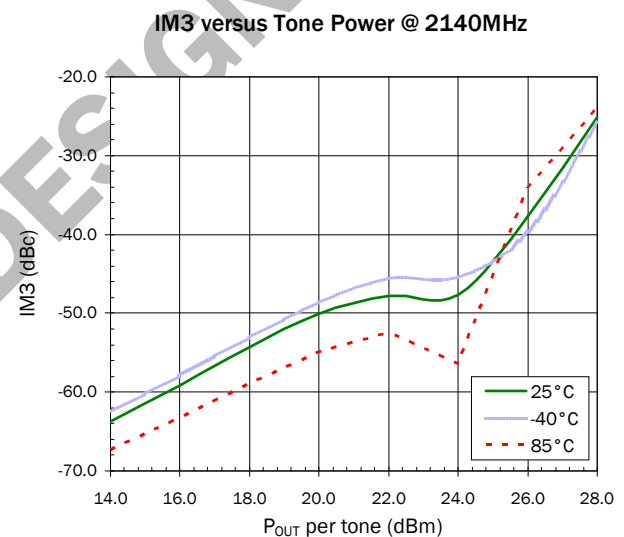
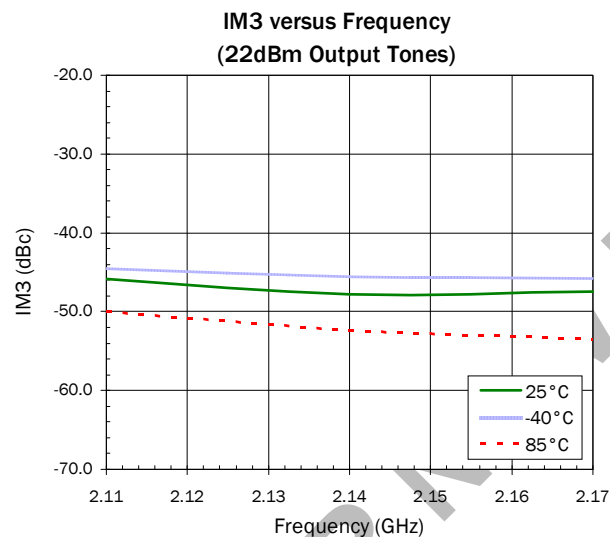
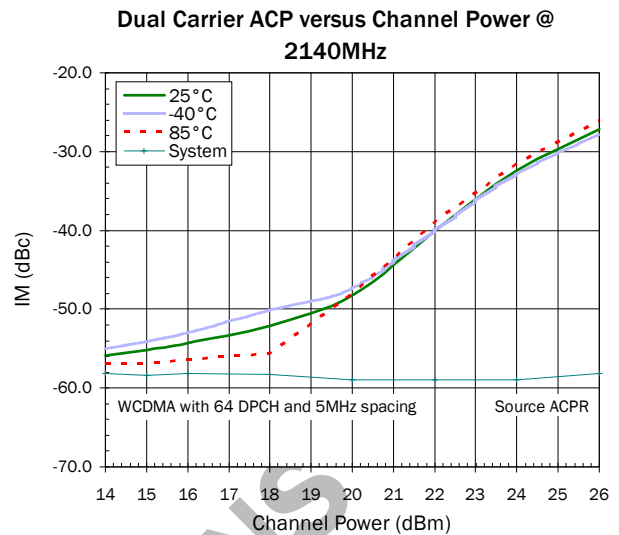
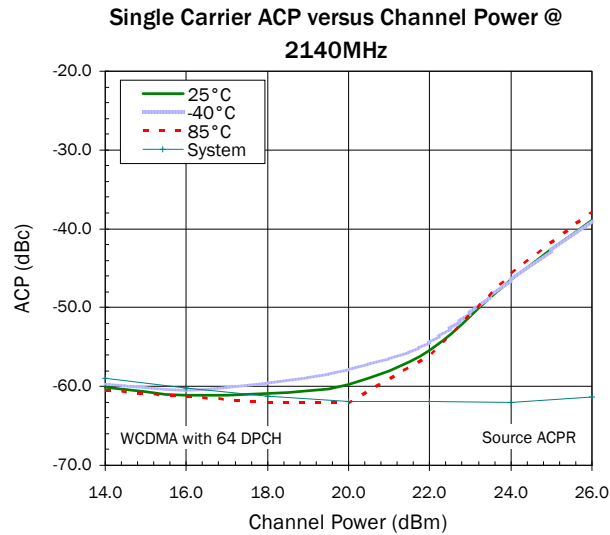
**S12 over Temperature**



**S22 over Temperature**

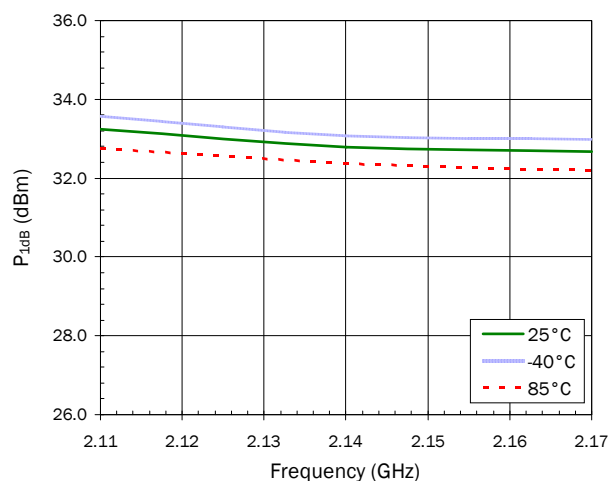


## Typical RF Performance (2110MHz to 2170MHz Application Circuit)

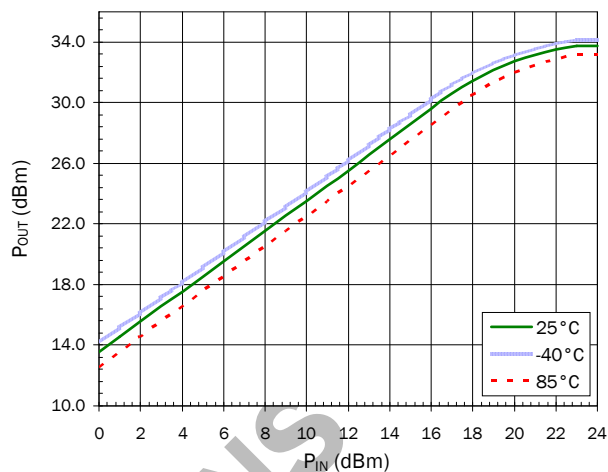


## Typical RF Performance (2110MHz to 2170MHz Application Circuit)

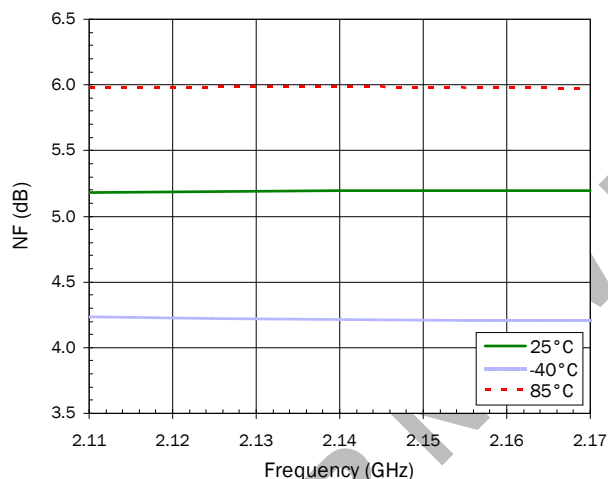
$P_{1dB}$  versus Frequency



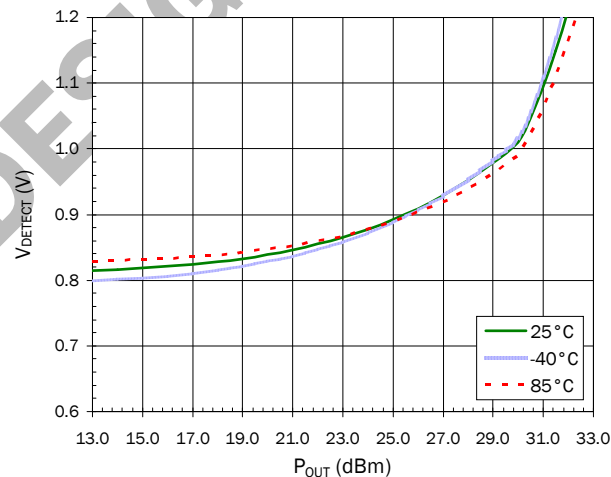
$P_{IN}$  versus  $P_{OUT}$  @ 2140MHz



Noise Figure vs. Frequency

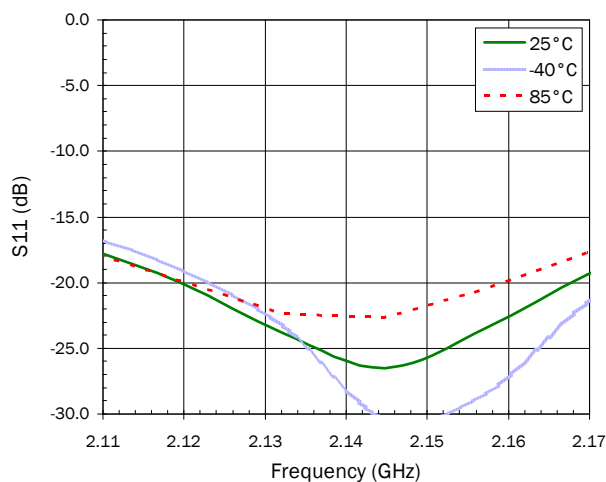


$V_{DETECT}$  versus  $P_{OUT}$  @ 2140MHz

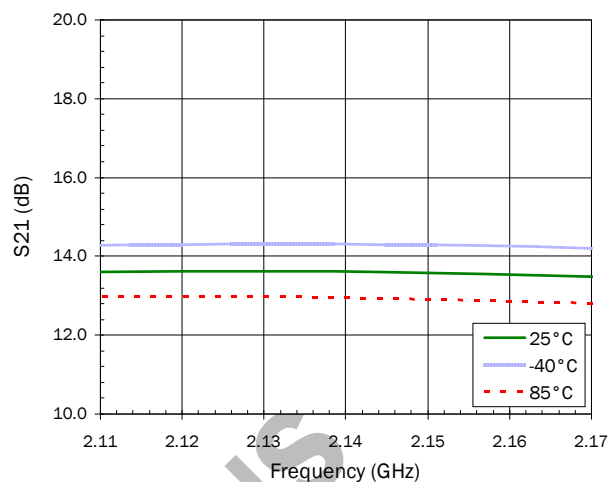


## S-Parameters over Temperature (2110MHz to 2170MHz Application Circuit)

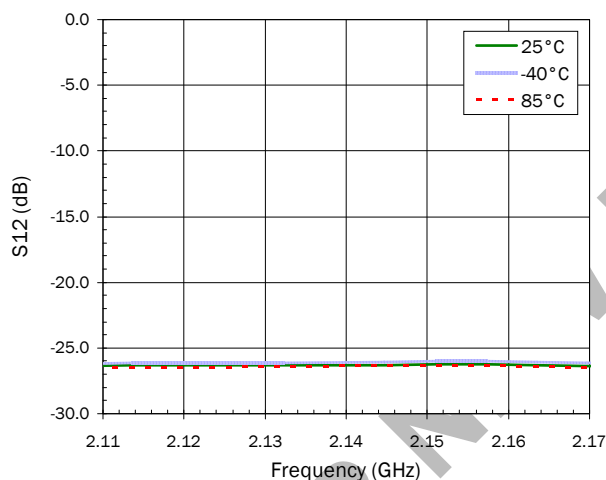
**S11 over Temperature**



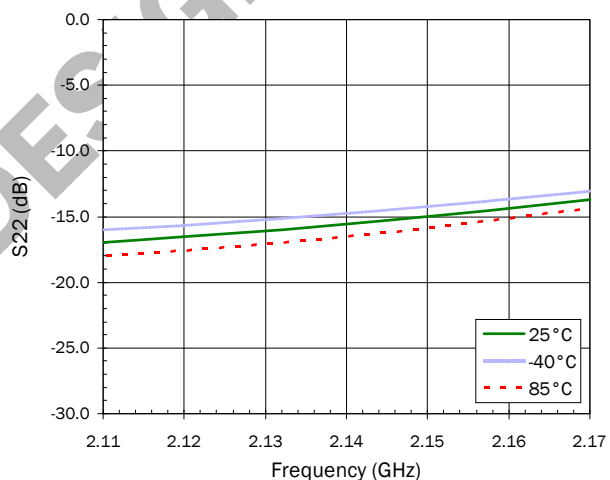
**S21 over Temperature**



**S12 over Temperature**



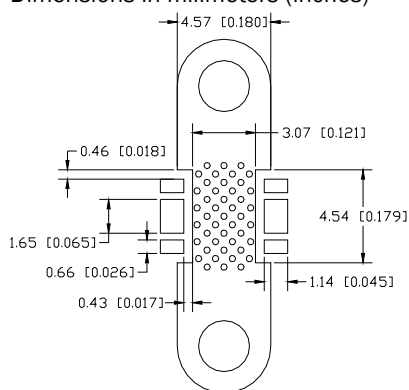
**S22 over Temperature**



| Pin | Function   | Description                                                                                                                                                                                                                                |
|-----|------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| 1   | VBIAS      | This is the supply voltage for the active bias circuit.                                                                                                                                                                                    |
| 2   | RF IN      | This is the RF input pin and has a DC voltage present. An external DC block is required.                                                                                                                                                   |
| 3   | VPC        | Power up/down control pin. The voltage on this pin should never exceed the voltage on pin 1 by more than 0.5V unless the supply current from pin 3 is limited <10mA.                                                                       |
| 4   | VDET       | This is the output port for the power detector. It samples the power at the input of the amplifier.                                                                                                                                        |
| 5   | RF OUT/VCC | This is the RF output pin and DC connection to the collector.                                                                                                                                                                              |
| 6   | NC         | Not connected                                                                                                                                                                                                                              |
| GND | GND        | These pins are DC connected to the backside paddle. They provide good thermal connection to the backside paddle for hand soldering and rework. Many thermal and electrical GND vias are required as shown in the recommended land pattern. |

## Suggested Pad Layout

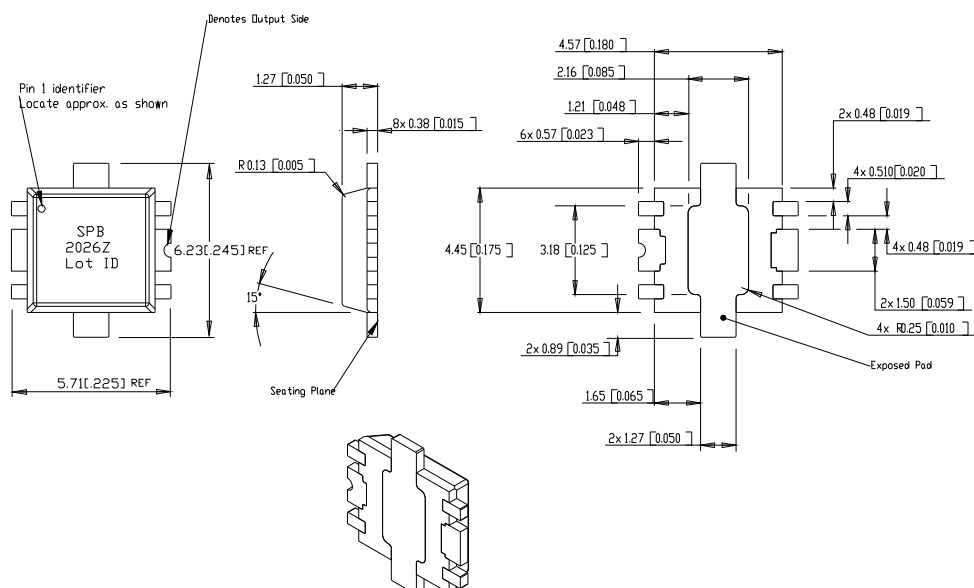
Dimensions in millimeters (inches)



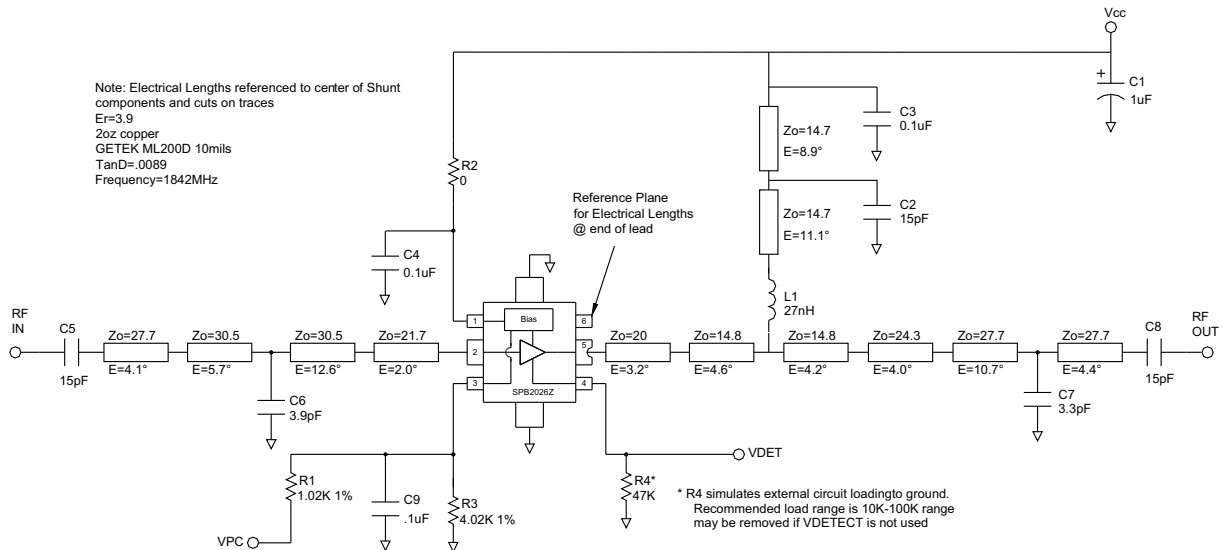
## Package Drawing

Dimensions in millimeters (inches)

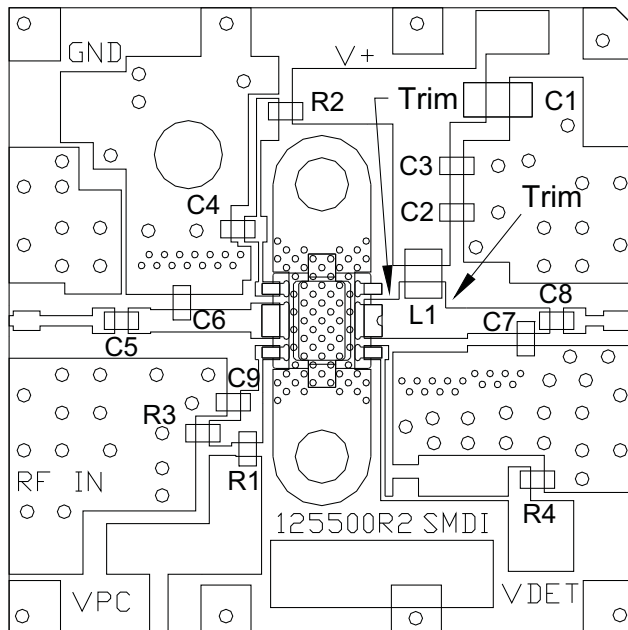
Refer to drawing posted at [www.rfmd.com](http://www.rfmd.com) for tolerances.



## 1805 MHz to 1880 MHz Application Schematic

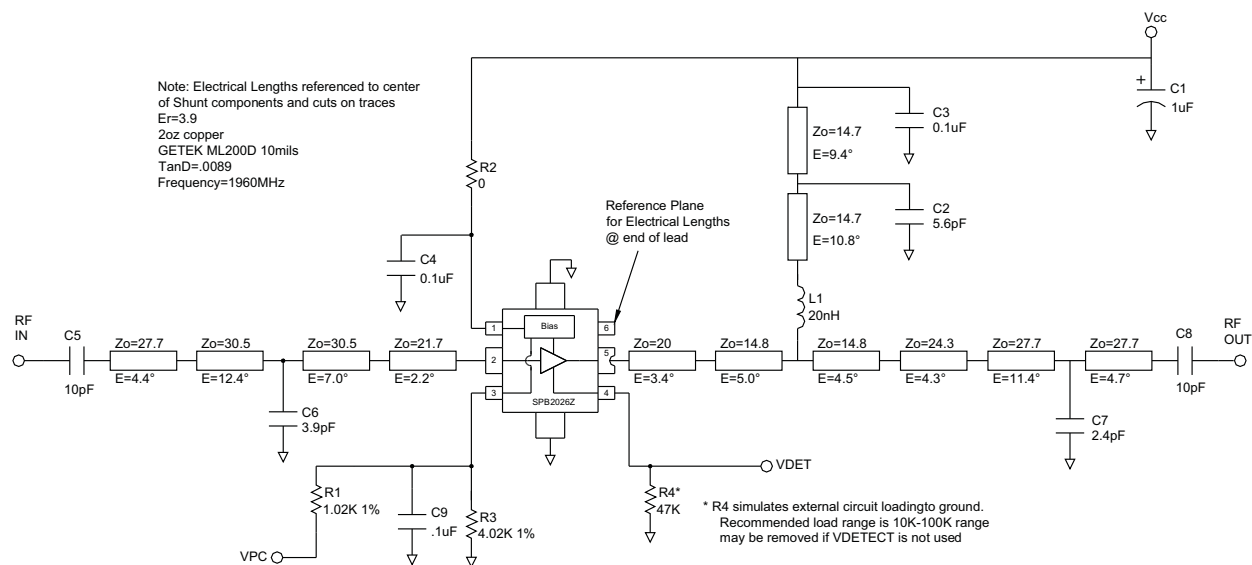


## 1805MHz to 1880MHz Evaluation Board Layout and Bill of Materials

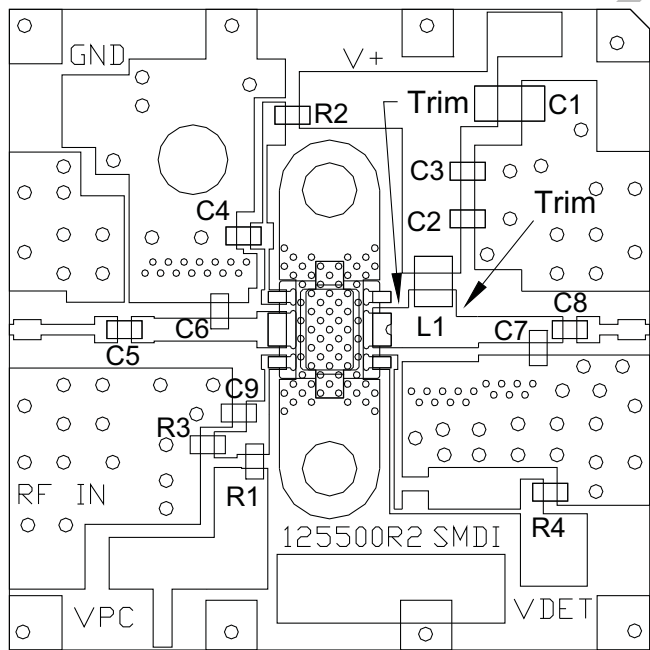


| DESG     | DESCRIPTION         |
|----------|---------------------|
| Q1       | SPB2026Z            |
| R1       | 1.02K OHM, 0603 1%  |
| R2       | 0 OHM, 0603         |
| R3       | 4.02K OHM, 0603 1%  |
| R4       | 47K OHM, 0603       |
| C1       | 1uF Tant.           |
| C2       | 15pF CAP, 0603 AVX  |
| C3,C4,C9 | 0.1uF CAP, 0603     |
| C5       | 15pF CAP, 0603 AVX  |
| C6       | 3.9pF CAP, 0603 AVX |
| C7       | 3.3pF CAP, 0603 AVX |
| C8       | 15pF CAP, 0603 AVX  |
| L1       | 27nH IND, CC 0805HQ |

1930MHz to 1990MHz Application Schematic

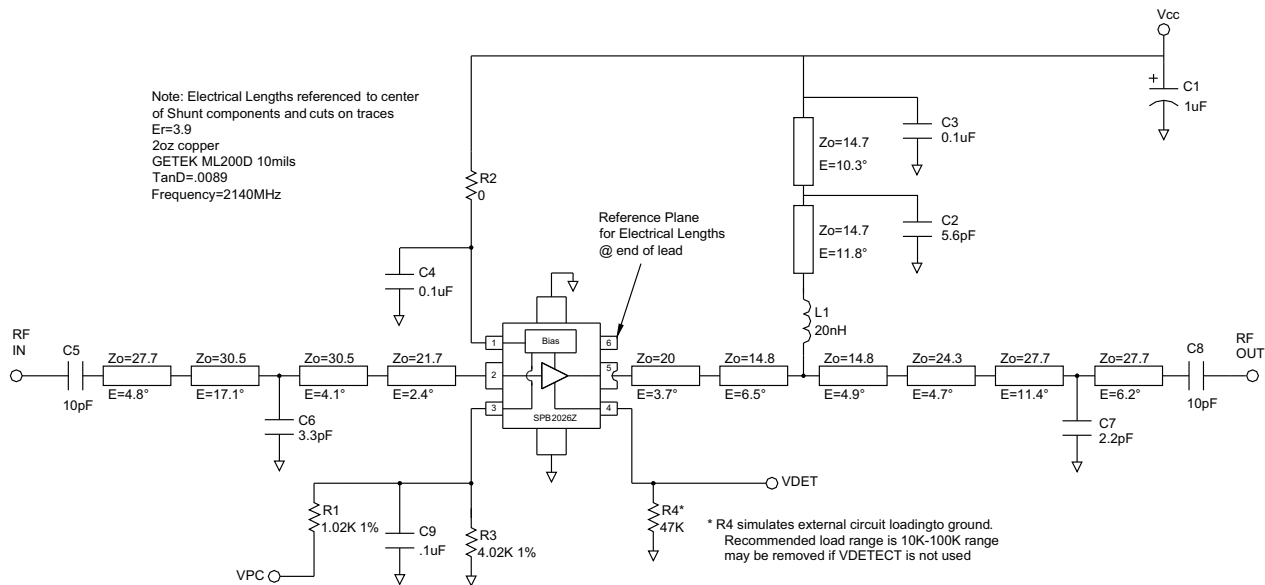


1930MHz to 1990MHz Evaluation Board Layout and Bill of Materials

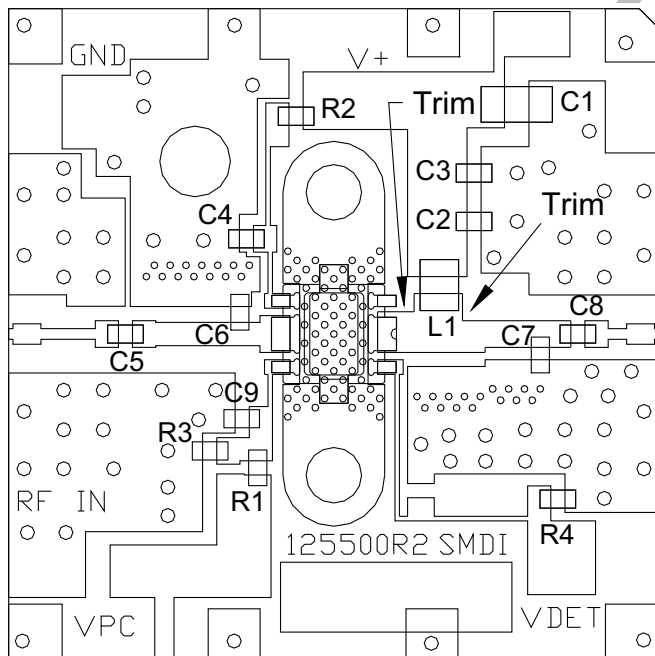


| DESG     | DESCRIPTION         |
|----------|---------------------|
| Q1       | SPB2026Z            |
| R1       | 1.02K OHM, 0603 1%  |
| R2       | 0 OHM, 0603         |
| R3       | 4.02K OHM, 0603 1%  |
| R4       | 47K OHM, 0603       |
| C1       | 1uF Tant.           |
| C2       | 5.6pF CAP, 0603 AVX |
| C3,C4,C9 | 0.1uF CAP, 0603     |
| C5       | 10pF CAP, 0603 AVX  |
| C6       | 3.9pF CAP, 0603 AVX |
| C7       | 2.4pF CAP, 0603 AVX |
| C8       | 10pF CAP, 0603 AVX  |
| L1       | 20nH IND, CC 0805HQ |

## 2110MHz to 2170MHz Application Schematic



## 2110MHz to 2170MHz Evaluation Board Layout and Bill of Materials



| DESG     | DESCRIPTION         |
|----------|---------------------|
| Q1       | SPB2026Z            |
| R1       | 1.02K OHM, 0603 1%  |
| R2       | 0 OHM, 0603         |
| R3       | 4.02K OHM, 0603 1%  |
| R4       | 47K OHM, 0603       |
| C1       | 1uF Tant.           |
| C2       | 5.6pF CAP, 0603 AVX |
| C3,C4,C9 | 0.1uF CAP, 0603     |
| C5       | 10pF CAP, 0603 AVX  |
| C6       | 3.3pF CAP, 0603 AVX |
| C7       | 2.2pF CAP, 0603 AVX |
| C8       | 10pF CAP, 0603 AVX  |
| L1       | 20nH IND, CC 0805HQ |

Part Identification

SPB2026Z on line one with Trace Code on line two.

Ordering Information

| Part Number  | Description                                     |
|--------------|-------------------------------------------------|
| SPB2026Z     | 7" Reel with 1000 pieces                        |
| SPB2026ZSQ   | Sample Bag with 25 pieces                       |
| SPB2026ZSR   | 7" Reel with 100 pieces                         |
| SPB2026ZPCK1 | 1805MHz to 1880MHz PCBA with 5 piece Sample Bag |
| SPB2026ZPCK2 | 1930MHz to 1990MHz PCBA with 5 piece Sample Bag |
| SPB2026ZPCK3 | 2110MHz to 2170MHz PCBA with 5 piece Sample Bag |

NOT FOR NEW DESIGNS